

$V_{RSM}, V_{RRM}$	V <sub>VRMS</sub>	$I_D = 18 \text{ A } (T_c = 75 ^{\circ}\text{C})$	C <sub>max</sub>	$R_{min}$
V	V	Types	μF	Ω
200	60	SKB 26/02		0,15
400	125	SKB 26/04		0,3
600	185	SKB 26/06		0,4
800	250	SKB 26/08		0,5
1000	310	SKB 26/10		0,65
1200	380	SKB 26/12		0,75
1400	440	SKB 26/14		0,9
1600	500	SKB 26/16		1

## Power Bridge Rectifiers

## **SKB 26**

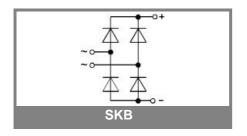
## **Features**

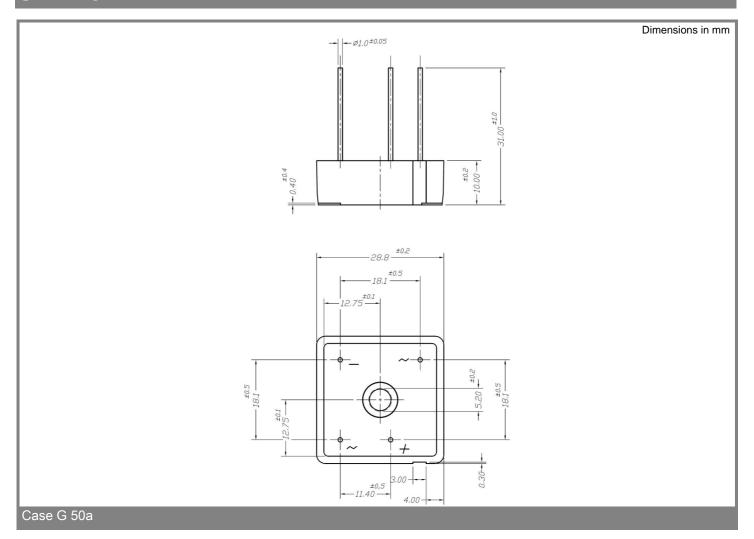
- Square plastic case with isolated metal base plate and wire leads
- Ideal for printed circuit boards
- Blocking voltage up to 1600 V
- High surge currents
- Notch moulded in casing for easy polarity identification
- · Easy chassis mounting

## **Typical Applications**

- Single phase rectifiers for power supplies
- Input rectifiers for variable frequency drives
- Rectifiers for DC motor field supplies
- · Battery charge rectifiers
- Recommended snubber network: RC:  $0.1 \mu F$ ,  $50 \Omega$  (P <sub>R</sub> = 1 W)
- Soldered directly onto a p.c.b. of 100 x
  160 mm with tinned tracking of min. 2.5
- 2) Mounted on a painted metal sheet of min.250 x 250 x 1 mm

Symbol	Conditions	Values	Units
I <sub>D</sub>	T <sub>a</sub> = 45 °C, isolated <sup>1)</sup>	3,5	Α
	T <sub>a</sub> = 45 °C, chassis <sup>2)</sup>	10	Α
I <sub>DCL</sub>	T <sub>a</sub> = 45 °C, isolated <sup>1)</sup>	3	Α
	T <sub>a</sub> = 45 °C, chassis <sup>2)</sup>	9,5	Α
	T <sub>a</sub> = 45 °C, P1A/120	14	Α
I <sub>FSM</sub>	T <sub>vi</sub> = 25 °C, 10 ms	370	Α
	T <sub>vi</sub> = 150 °C, 10 ms	320	Α
i²t	T <sub>vj</sub> = 25 °C, 8,3 10 ms	680	A²s
	T <sub>vj</sub> = 150 °C, 8,3 10 ms	500	A²s
V <sub>F</sub>	T <sub>vi</sub> = 25°C, I <sub>F</sub> = 150 A	max. 2,2	V
V <sub>(TO)</sub>	T <sub>vj</sub> = 150°C	max. 0,85	V
r <sub>T</sub>	T <sub>vj</sub> = 150°C	max. 12	mΩ
$I_{RD}$	$T_{vj} = 25$ °C, $V_{RD} = V_{RRM}$	300	μA
	$T_{vj}^{3} = {^{\circ}C}, V_{RD} = V_{RRM} \ge V$		μA
$I_{RD}$	$T_{vj} = 150$ °C, $V_{RD} = V_{RRM}$	5	mA
	$T_{vj}^{\circ} = {^{\circ}C}, V_{RD} = V_{RRM} \ge V$		mA
t <sub>rr</sub>	$T_{vj} = 25$ °C	10	μs
$f_G$		2000	Hz
R <sub>th(j-a)</sub>	isolated <sup>1)</sup>	15	K/W
	chassis <sup>2)</sup>	4,7	K/W
R <sub>th(j-c)</sub>	total	1,9	K/W
R <sub>th(c-s)</sub>	total	0,15	K/W
T <sub>vi</sub>		- 40 <b>+</b> 150	°C
T <sub>stg</sub>		- 55 <b>+</b> 150	°C
V <sub>isol</sub>	a. c. 50 60 Hz; r.m.s.; 1 s / 1 min.	3000 / 2500	V~
M <sub>s</sub>	to heatsink	2 ± 15 %	Nm
M <sub>t</sub>			Nm
a			m/s²
w		20	g
Fu			А
Case		G 50a	





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